

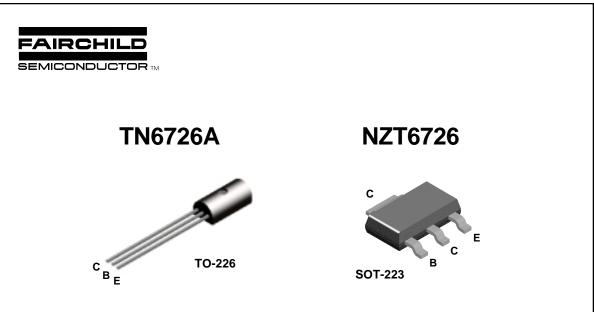
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PNP General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.0 A. Sourced from Process 77.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	1.5	А
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		TN6726A	*NZT6726	
P _D	Total Device Dissipation	1.0	1.0	W
	Derate above 25°C	8.0	8.0	mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	125	°C/W

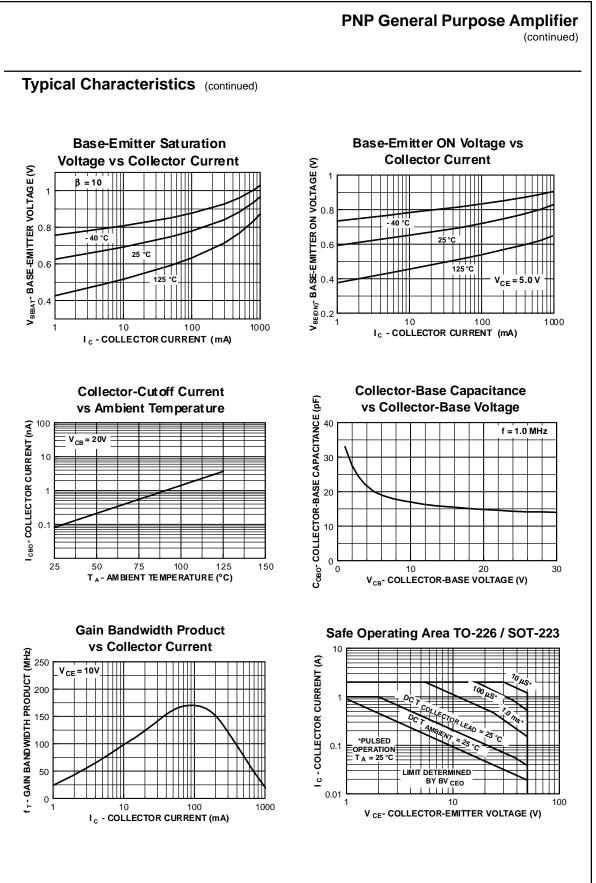
*Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

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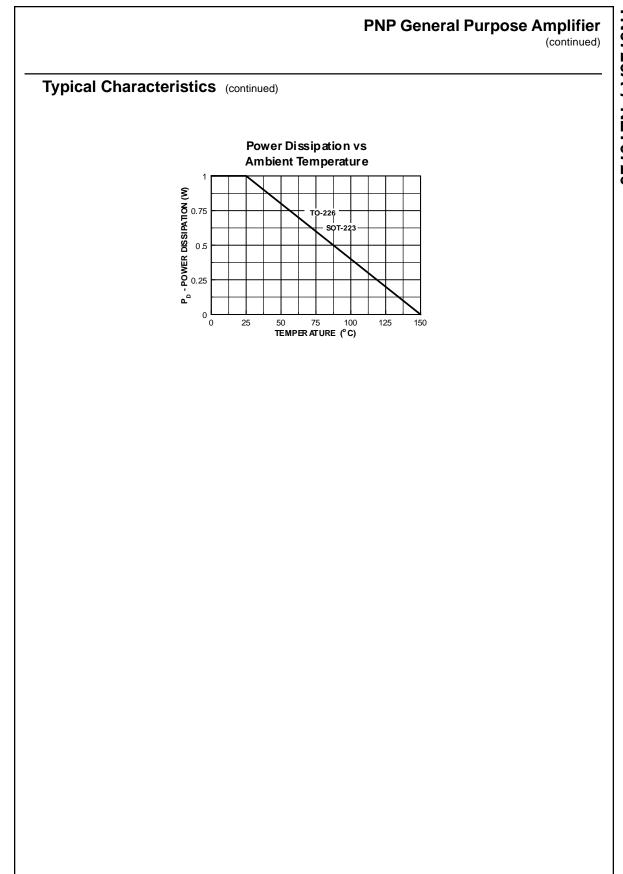
PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
	RACTERISTICS				
	Collector-Emitter Breakdown	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0$	30	Τ	V
V _{(BR)CBO}	Voltage Collector-Base Breakdown Voltage	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm E} = 0$	40	-	V
(BR)EBO	Emitter-Base Breakdown Voltage	$I_E = 100 \ \mu\text{A}, I_C = 0$	5.0	-	V
CBO	Collector-Cutoff Current	$V_{CB} = 40 \text{ V}, \text{ I}_{E} = 0$	0.0	0.1	μA
BO	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_C = 0$	-	0.1	μΑ
			<u>.</u>		
N CHAR	ACTERISTICS*				
FE	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	55		
		$I_{C} = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$	60 50	250	
CE(sat)	Collector-Emitter Saturation Voltage	$I_{C} = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 1.0 \text{ A}, I_{B} = 100 \text{ mA}$	50	0.5	V
BE(on)	Base-Emitter On Voltage	I _C = 1.0 A, V _{CE} = 1.0 V		1.2	V
			<u>,</u>	<u>,</u>	
MALL SI	GNAL CHARACTERISTICS				
lfe	Small-Signal Current Gain	$I_{c} = 50 \text{ mA}, V_{CE} = 10 \text{ V},$	2.5	25	
		f = 20 MHz			
*Pulse Test: P	Collector-Base Capacitance ulse Width \leq 300 μ s, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP to	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz}$ ransistors.		30	pF
*Pulse Test: P NOTE: All volta	ulse Width \leq 300 μ s, Duty Cycle \leq 1.0%			30	pF
*Pulse Test: P NOTE: All volta	ulse Width ≤ 300 μs, Duty Cycle ≤ 1.0% ages (V) and currents (A) are negative polarity for PNP tr	ransistors. Collector-E	Emitter S		
*Pulse Test: P NOTE: All volta Typica	ulse Width \leq 300 μ s, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP tr Al Characteristics	ransistors. Collector-E		aturation	1
NOTE: All volta	ulse Width ≤ 300 µs, Duty Cycle ≤ 1.0% ages (V) and currents (A) are negative polarity for PNP tr al Characteristics Typical Pulsed Current Gain vs Collector Current	ransistors. Collector-E		aturation	1
*Pulse Test: P NOTE: All volta Typica	ulse Width ≤ 300 µs, Duty Cycle ≤ 1.0% ages (V) and currents (A) are negative polarity for PNP tr al Characteristics Typical Pulsed Current Gain	ransistors. Collector-E		aturation	1
*Pulse Test: P NOTE: All volta Typica	ulse Width \leq 300 µs, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP tr al Characteristics Fypical Pulsed Current Gain vs Collector Current	ransistors. Collector-E		aturation	1
*Pulse Test: P NOTE: All volta Typica	ulse Width ≤ 300 µs, Duty Cycle ≤ 1.0% ages (V) and currents (A) are negative polarity for PNP tr al Characteristics Typical Pulsed Current Gain vs Collector Current	ransistors. Collector-E		aturation r Curren	1
*Pulse Test: P NOTE: All volta Typica	ulse Width \leq 300 µs, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP to al Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0^{\circ}$	ransistors. Collector-E		aturation r Current	1
*Pulse Test: P NOTE: All volta Typica	ulse Width \leq 300 µs, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP tr al Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$	ransistors. Collector-E			
*Pulse Test: P NOTE: All volta Typica	ulse Width \leq 300 µs, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP to al Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0^{\circ}$	ransistors. Collector-E			1
*Pulse Test: P NOTE: All volta	ulse Width \leq 300 µs, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP tr al Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$	ransistors. Collector-E			
	ulse Width \leq 300 µs, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP tr al Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$	ransistors. Collector-E Voltage vs $1 \qquad \beta = 10$ $0.6 \qquad \beta = 10$ $0.6 \qquad 0.4$ $0.6 \qquad 0.4$		aturation r Current 40 °C	

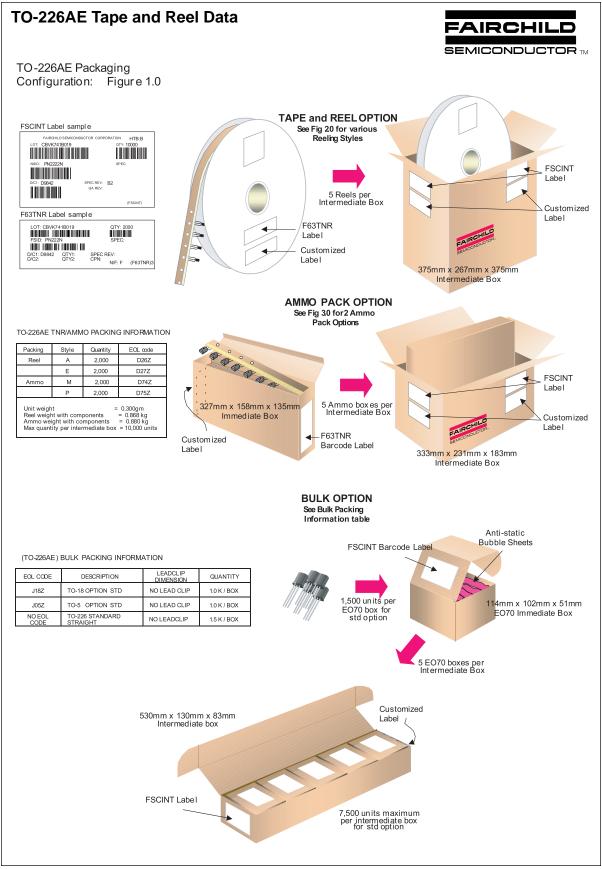
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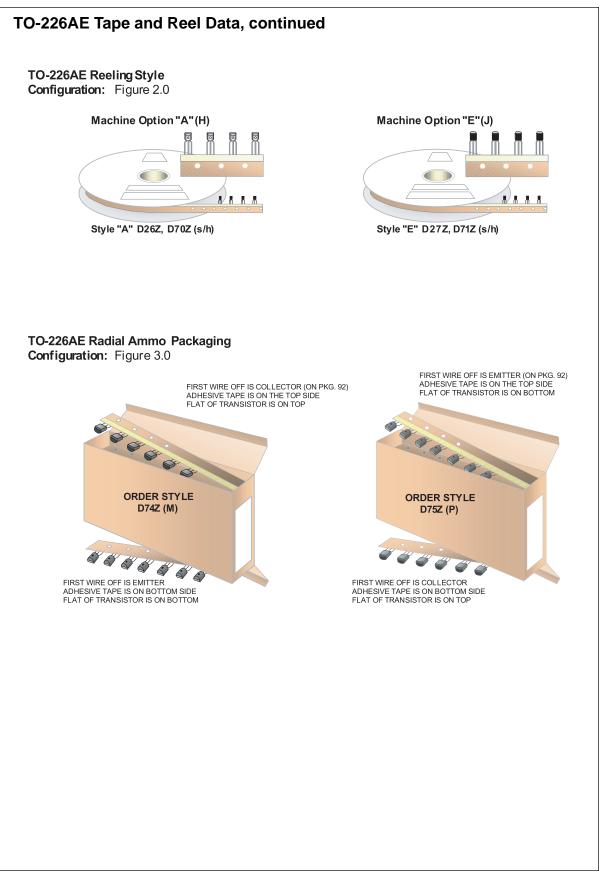


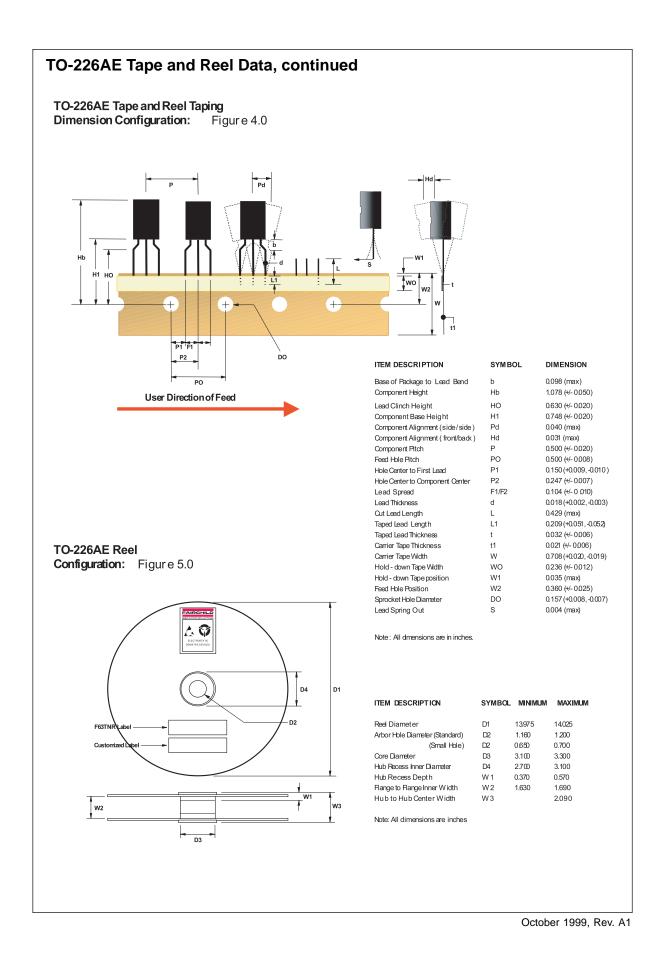
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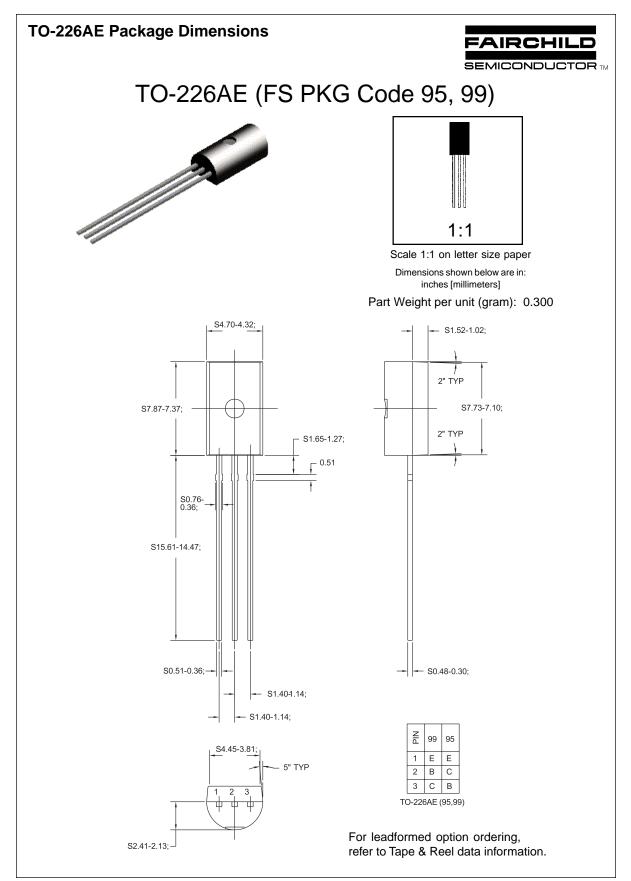


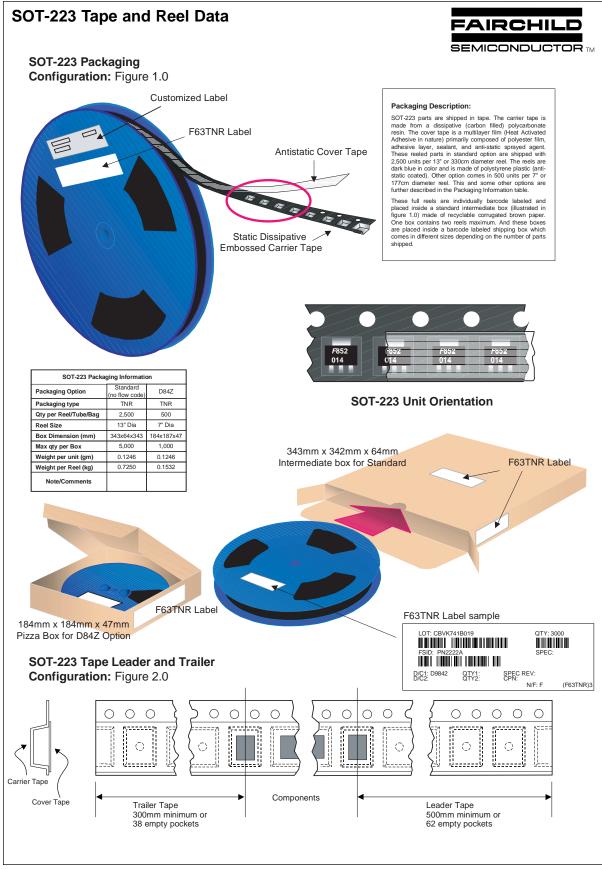
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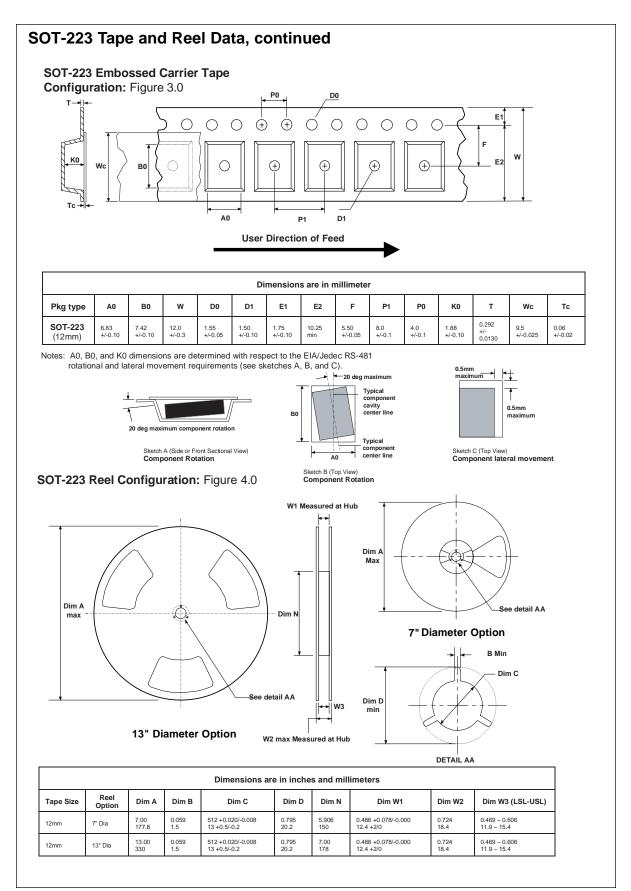


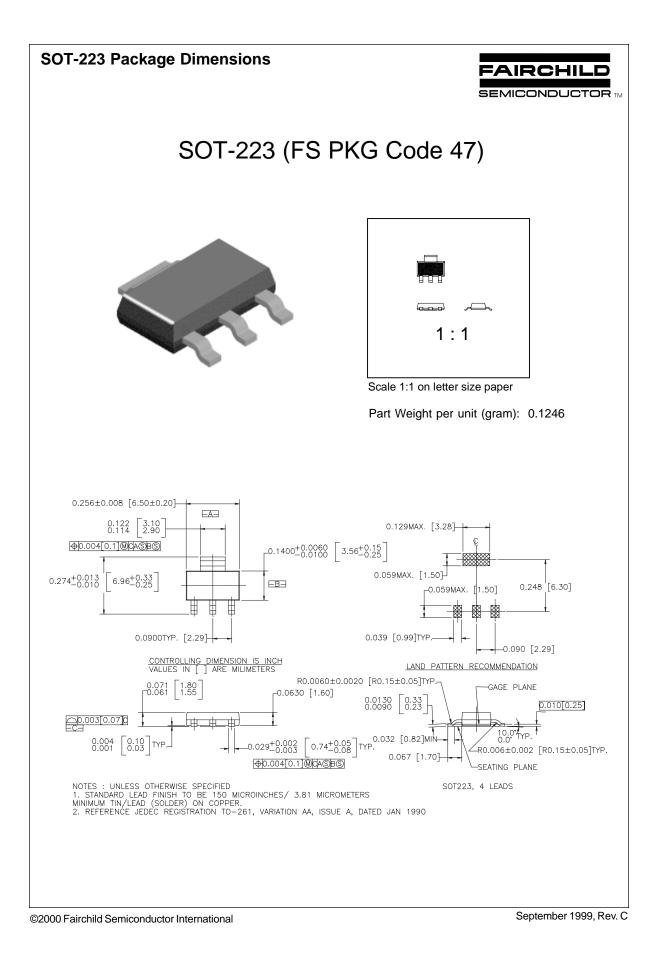




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